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# FDP032N08B N 沟道 PowerTrench<sup>®</sup> MOSFET 80 V、211 A、3.3 mΩ

### 特性

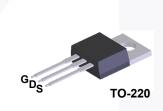
- $R_{DS(on)}$  = 2.85 m $\Omega$  (Typ.)@V<sub>GS</sub> = 10 V, I<sub>D</sub> = 50 A
- 低 FOM R<sub>DS(on)</sub> \* Q<sub>G</sub>
- 低反向恢复电荷, Q<sub>rr</sub>
- 软反向恢复体二极管
- 可实现高效同步整流
- 快速开关速度
- 100% 经过 UIL 测试
- 符合 RoHS 标准

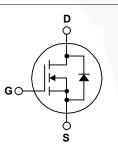
# 说明

此 N 沟道 MOSFET 采用飞兆半导体先进的 PowerTrench<sup>®</sup> 工艺 生产,这一先进工艺是专为最大限度地降低导通电阻并保持卓越 开关性能而定制的。

# 应用

- 用于 ATX/ 服务器 / 电信 PSU 的同步整流
- 电池保护电路
- 电机驱动和不间断电源
- 可再生系统





# MOSFET 最大额定值 T<sub>C</sub>=25℃ 除非另有说明。

符号		参数			
V <sub>DSS</sub>	漏极 - 源极电压				
V <sub>GSS</sub>	栅极 - 源极电压		±20	V	
		- 连续 (T <sub>C</sub> =25°C,硅限制)	211*		
I <sub>D</sub>	漏极电流			Α	
		- 连续 (T <sub>C</sub> =25°C,封装限制)	120	ſ	
I <sub>DM</sub>	漏极电流	- 脉冲 (说明 1)	844	Α	
E <sub>AS</sub>	单脉冲雪崩能量	(说明 2)	649	mJ	
dv/dt	二极管恢复 dv/dt 峰值	(说明 3)	6.0	V/ns	
D	-1 +7	(T <sub>C</sub> = 25°C)	263	W	
P <sub>D</sub>	功耗	- 降低至 25°C 以上	1.75	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	工作和存储温度范围		-55 至 +175	°C	
TL	用于焊接的最大引线温度,距离	300	°C		

\* 封装限制电流为 120 安。

# 热性能

符号	参数	FDP032N08B_F102	单位
$R_{ ext{ heta}JC}$	结至外壳热阻最大值	0.57	°C/W
$R_{ ext{ heta}JA}$	结至环境热阻最大值	62.5	0/11

2014年2月

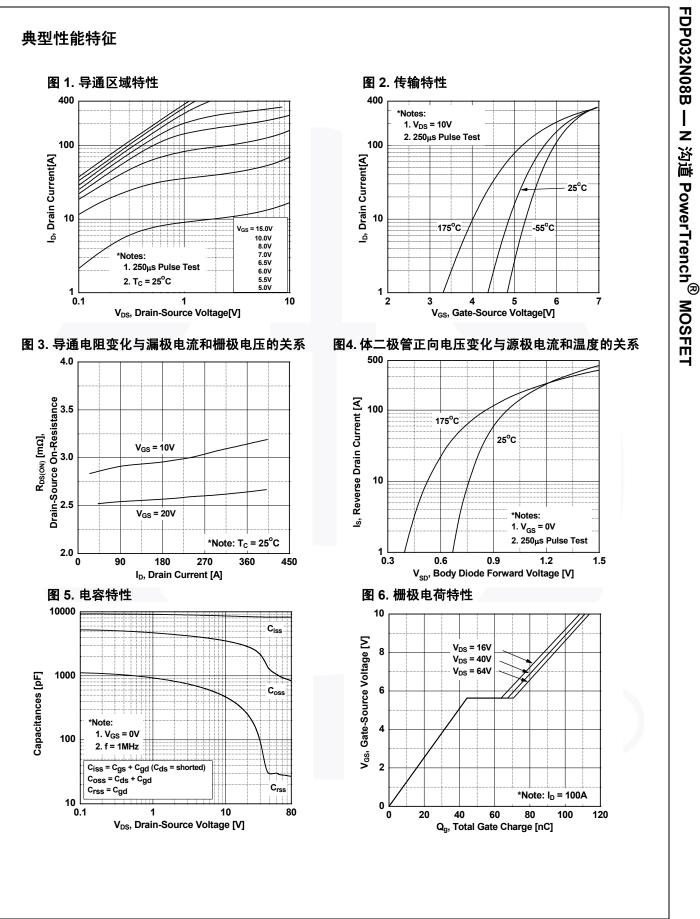
器件编号 顶标 封装   FDP032N08B F102 FDP032N08B TO-22		封装	包装方法	卷尺寸		带宽	数量		
		TO-220			N/A		<u>               50</u> 个		
			I						
电气特性	T <sub>C</sub> =25°C 隊	余非另有说明。							
符号		参数		测试条件		最小值	典型值	最大值	单位
关断特性									
BV <sub>DSS</sub>	漏极一源	极击穿电压		I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V		80	-	-	V
$\Delta BV_{DSS}$		温度系数		I <sub>D</sub> =250 μA,温度为 25 <sup>6</sup>		-	0.04	-	V/°C
/ ΔT <sub>J</sub>				5	-	-		4	
I <sub>DSS</sub>	零栅极电	电压漏极电流			$V_{DS} = 64 V, V_{GS} = 0 V$		-	1	μA
	栅极一体	温中淬		$V_{DS} = 64 \text{ V}, \text{ T}_{C} = 150^{\circ}\text{ (}$		-	-	500 ±100	nA
I <sub>GSS</sub>	伽加及一件	<b>胂电</b> 流	-	$V_{GS} = \pm 20 V, V_{DS} = 0 V$		-	-	100	IIA
导通特性									
V <sub>GS(th)</sub>	栅极阈值电压			$V_{GS} = V_{DS}, I_{D} = 250 \ \mu A$		2.5	-	4.5	V
R <sub>DS(on)</sub>	漏极至源极静态导通电阻			V <sub>GS</sub> = 10 V, I <sub>D</sub> = 100 A		-	2.85	3.3	mΩ
9 <sub>FS</sub>	正向跨导			V <sub>DS</sub> = 10 V, I <sub>D</sub> = 100 A		-	168	-	S
动态特性									
C <sub>iss</sub>	输入电容			V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, f = 1 MHz		-	8245	10965	pF
C <sub>oss</sub>	输出电容					-	1250	1660	pF
C <sub>rss</sub>	反向传输	电容				-	28	-	pF
C <sub>oss(er)</sub>	能量相关输出电容			$V_{DS}$ = 40 V, $V_{GS}$ = 0 V		-	2337	-	pF
Q <sub>g(tot)</sub>	10 V 的栅	·极电荷总量	量			-	111	144	nC
Q <sub>gs</sub>	栅极 - 源	极栅极电荷		$V_{DS} = 40 \text{ V}, \text{ I}_{D} = 100 \text{ A},$	,	-	44	-	nC
Q <sub>gd</sub>	栅极 - 漏	极 " 米勒 " 电荷		V <sub>GS</sub> = 10 V		-	23	-	nC
V <sub>plateau</sub>	栅极平台	电压			(说明4)	-	5.6	-	V
Q <sub>sync</sub>	总栅极电	荷同步		$V_{DS} = 0 V, I_{D} = 50 A$		-	98.2	-	nC
Q <sub>oss</sub>	输出电荷			$V_{DS}$ = 40 V, $V_{GS}$ = 0 V		-	114	-	nC
ESR	等效串联	电阻 (G-S)		f = 1 MHz		-	2.3	-	Ω
开关特性									
t <sub>d(on)</sub>	导通延迟时间					-	38	86	ns
t <sub>r</sub>	开通上升I			V <sub>DD</sub> = 40 V, I <sub>D</sub> = 100 A		7 -	44	97	ns
t <sub>d(off)</sub>	关断延迟	时间		V <sub>GS</sub> = 10 V, R <sub>G</sub> = 4.7 Ω		-	71	152	ns
t <sub>f</sub>	关断下降I	时间			(说明4)	-	31	72	ns
漏极 - 源极.	二极管特	性						7.	
l <sub>s</sub>		▪ <u></u>	卖电流			-	-	211	Α
I <sub>SM</sub>		<u>级二极官最大正向</u> 座。 极二极管最大正向脉冲				-		844	A

۱ <sub>S</sub>	漏极 - 源极二极管最大正向连续电流		-	-	211	A
I <sub>SM</sub>	漏极 - 源极二极管最大正向脉冲电流		-	-	844	А
$V_{SD}$	漏极 - 源极二极管正向电压	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 100 A	-	-	1.3	V
t <sub>rr</sub>	反向恢复时间	V <sub>GS</sub> = 0 V, V <sub>DD</sub> = 40 V, I <sub>SD</sub> = 100 A,	-	75		ns
Q <sub>rr</sub>	反向恢复电荷	dI <sub>F</sub> /dt = 100 A/µs	-	102		nC

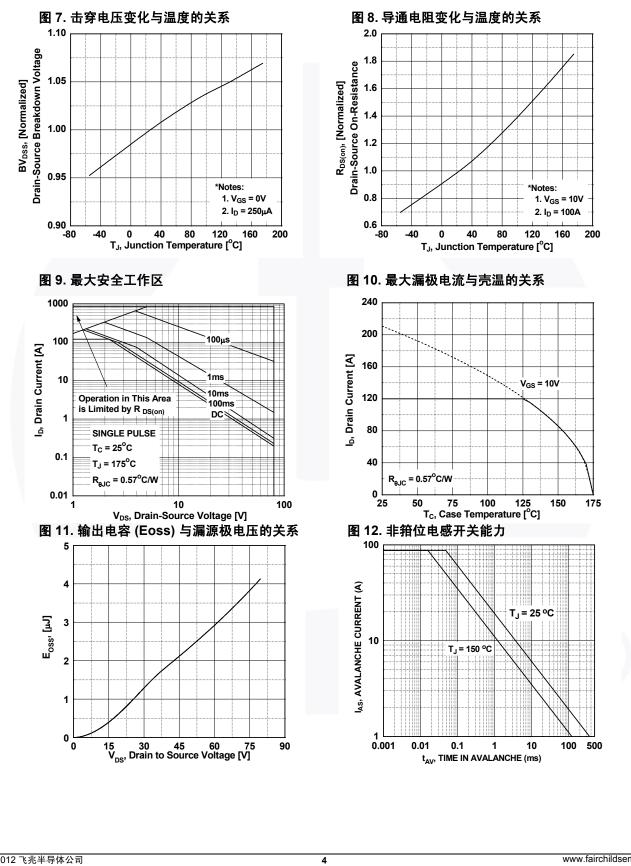
注意:

1. 重复额定值: 脉冲宽度受限于最大结温。 2. L=3 mH, I<sub>AS</sub>=20.8 A, 开始 T<sub>J</sub>=25°C。 3. I<sub>SD</sub> ≤ 100 A, di/dt ≤ 200 A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, 开始 T<sub>J</sub>=25°C。 4. 本质上独立于工作温度的典型特性。

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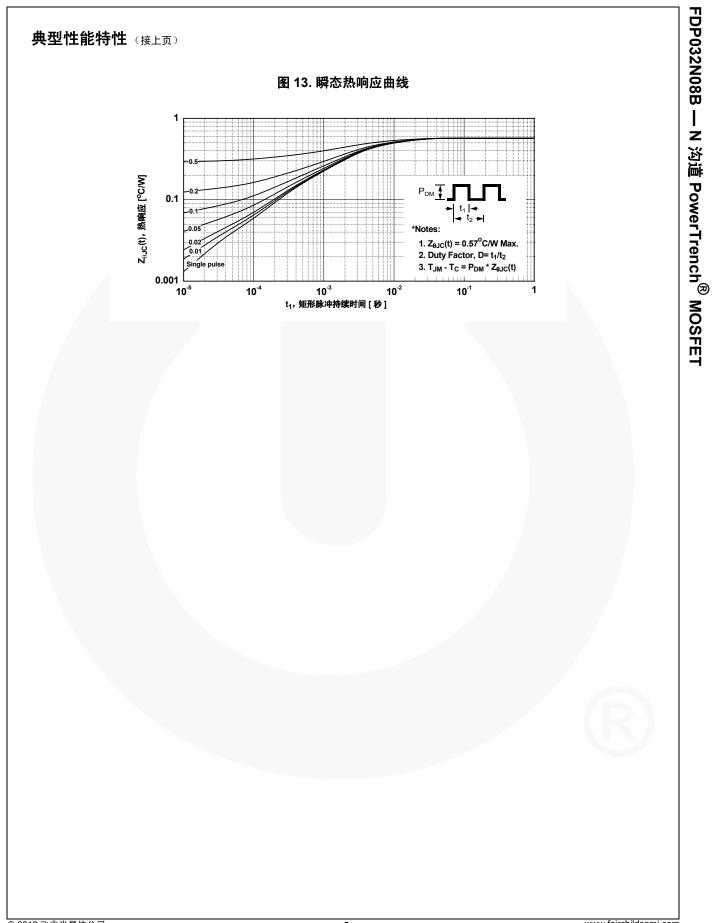


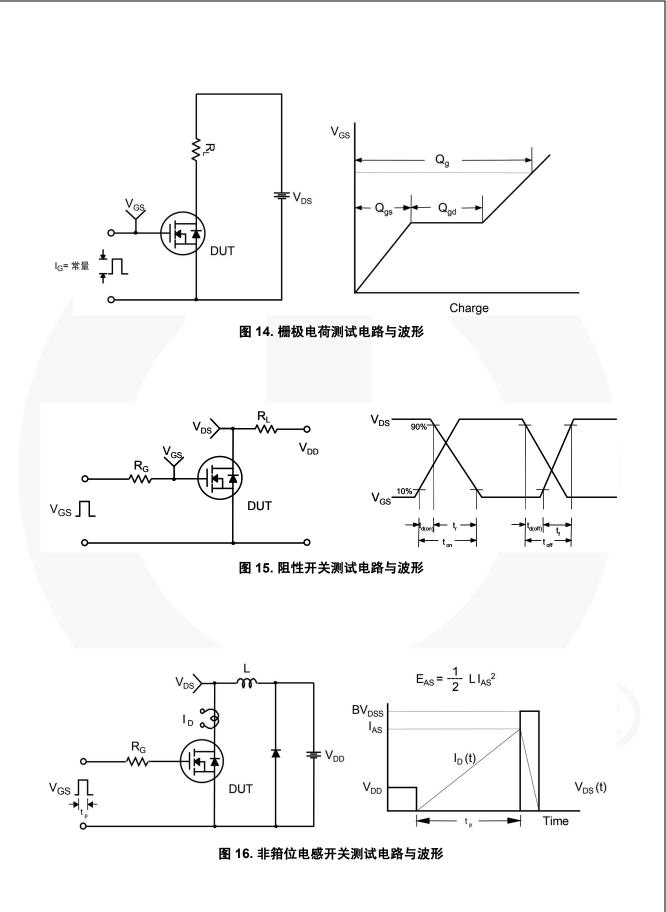
# 典型性能特性 (接上页)



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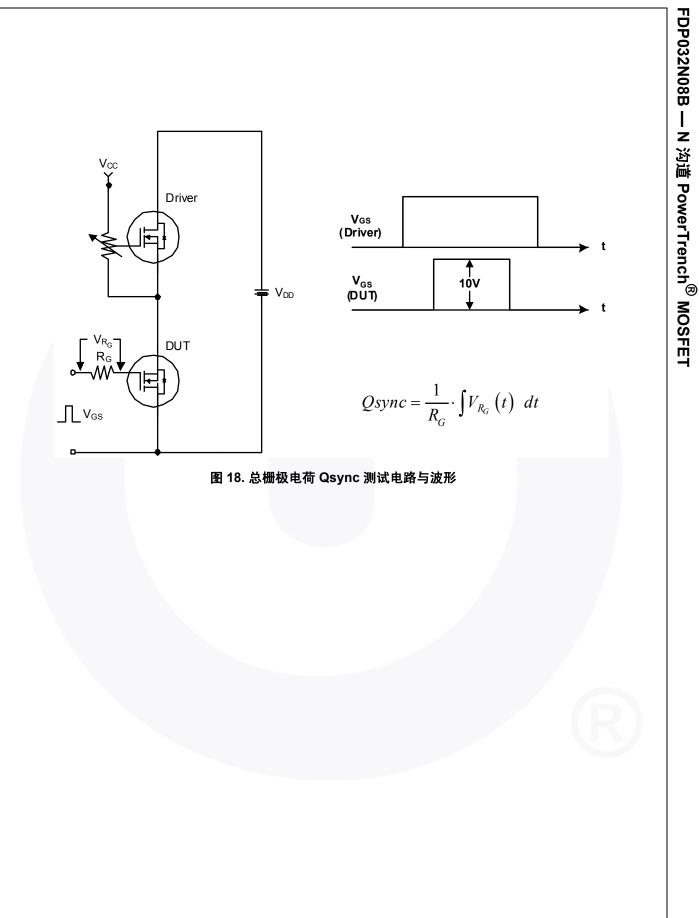


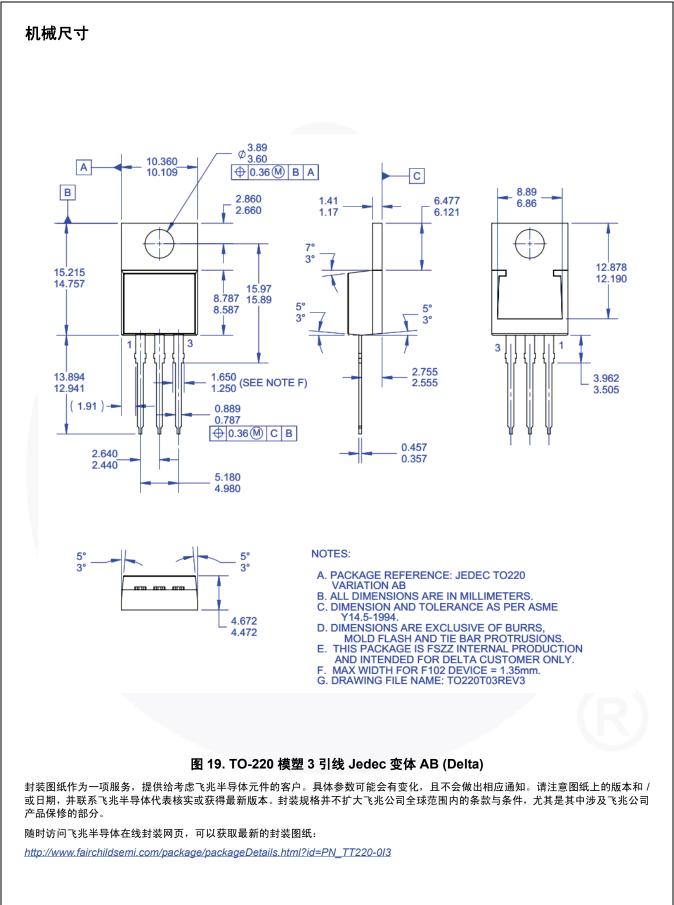


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DUT +  $v_{DS}$ ۱<sub>SD</sub> م a L Driver R<sub>G</sub> Same Type as DUT L F ∨<sub>DD</sub> ∏∏ v<sub>gs</sub> • dv/dt controlled by  $R_{G}$ • I<sub>SD</sub> controlled by pulse period ſ Gate Pulse Width V<sub>GS</sub> D = Gate Pulse Period 10V (Driver)  $\mathbf{I}_{\text{FM}}$  , Body Diode Forward Current I <sub>SD</sub> di/dt (DUT)  $I_{RM}$ Body Diode Reverse Current  $V_{DS}$ (DUT) Body Diode Recovery dv/dt  $V_{SD}$ V<sub>PD</sub> Body Diode Forward Voltage Drop 图 17. 二极管恢复 dv/dt 峰值测试电路与波形

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